



6NM65-S

Power MOSFET

6A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

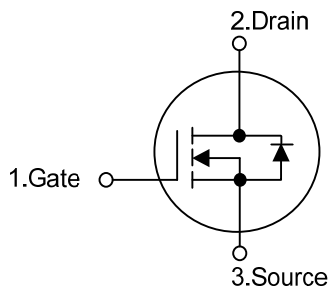
DESCRIPTION

The UTC **6NM65-S** is a Super Junction MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 1.4\Omega @ V_{GS} = 10V, I_D = 3.0A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

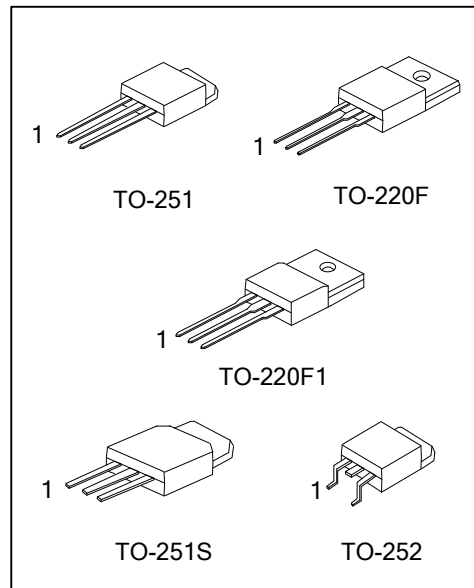


ORDERING INFORMATION

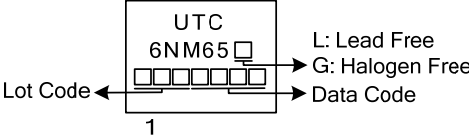
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6NM65L-TF3-T	6NM65G-TF3-T	TO-220F	G	D	S	Tube
6NM65L-TF1-T	6NM65G-TF1-T	TO-220F1	G	D	S	Tube
6NM65L-TM3-T	6NM65G-TM3-T	TO-251	G	D	S	Tube
6NM65L-TMS-T	6NM65G-TMS-T	TO-251S	G	D	S	Tube
6NM65L-TN3-R	6NM65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>6NM65L-TF3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TF3: TO-220F, TF1: TO-220F1, TM3: TO-251, TMS: TO-251S, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	6.0	A
	Pulsed (Note2)	I_{DM}	24	A
Avalanche Current (Note 2)		I_{AR}	1.4	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	141	mJ
Peak Diode Recovery dv/dt (Note4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F/TO-220F1	P_D	40	W
	TO-251/TO-251S		55	W
	TO-252			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=144\text{mH}$, $I_{AS}=1.4\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 6.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL RESISTANCES CHARACTERISTICS

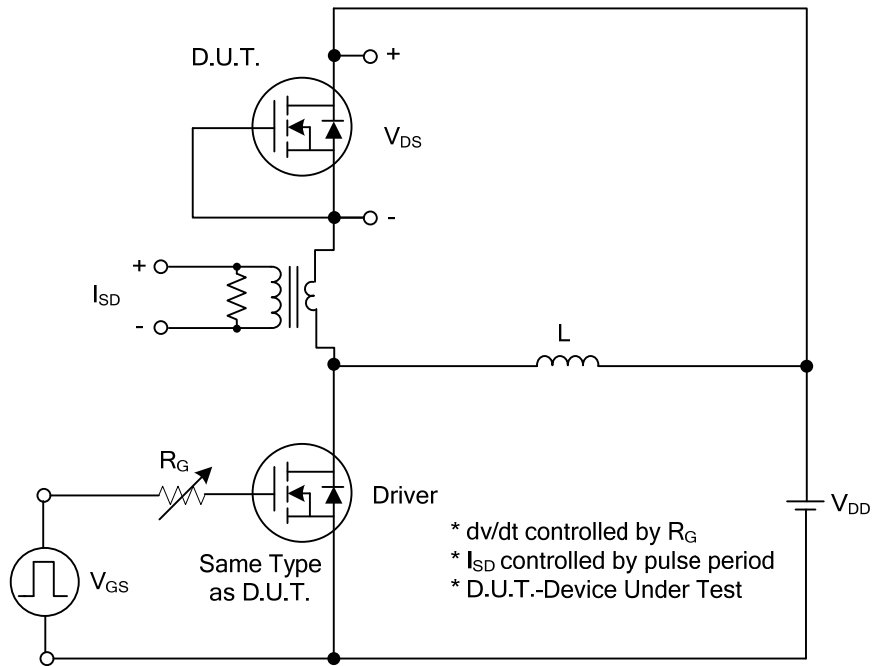
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-251/TO-252			
Junction to Case	TO-220F/TO-220F1	θ_{JC}	3.13	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S			
	TO-252			

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

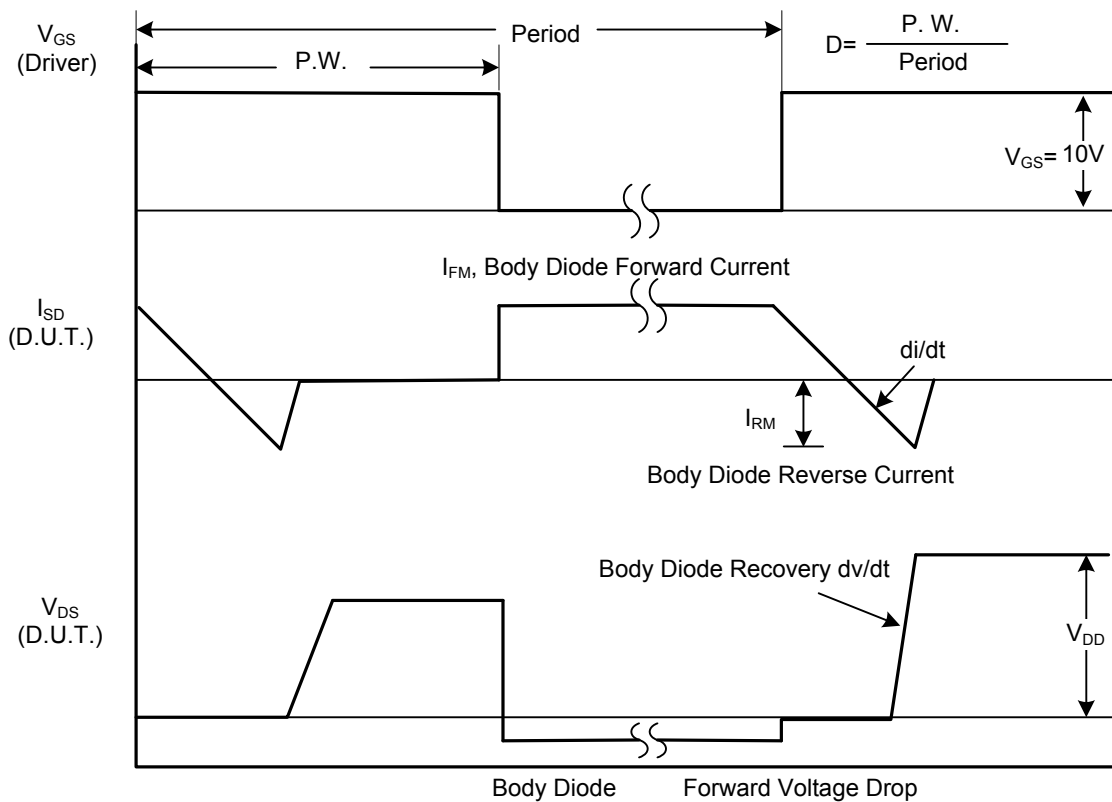
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	650			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	μA	
Gate-Source Leakage Current	Forward	I _{GSS}			100	nA	
	Reverse						V _{GS} = 30 V, V _{DS} = 0 V
		V _{GS} = -30 V, V _{DS} = 0 V			-100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.5		4.5	V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.0A			1.4	Ω	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1MHz		255		pF	
Output Capacitance	C _{OSS}				179		pF
Reverse Transfer Capacitance	C _{RSS}				24		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A, I _G = 100μA (Note 1, 2)		36		nC	
Gate to Source Charge	Q _{GS}				2.8		nC
Gate to Drain Charge	Q _{GD}				7.8		nC
Turn-ON Delay Time (Note 1)	t _{D(ON)}	V _{DD} = 30V, V _{GS} = 10V, I _D = 0.5A, R _G = 25Ω (Note 1, 2)		43		ns	
Rise Time	t _R				146		ns
Turn-OFF Delay Time	t _{D(OFF)}				260		ns
Fall-Time	t _F				90		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current	I _S				6.0	A	
Maximum Body-Diode Pulsed Current	I _{SM}				24	A	
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	V _{GS} = 0 V, I _S = 6.0A			1.4	V	
Body Diode Reverse Recovery Time (Note 1)	t _{rr}	V _{GS} =0V, I _S =6.0A dI _F /dt=100A/μs		260		ns	
Body Diode Reverse Recovery Charge	Q _{rr}				2.1		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

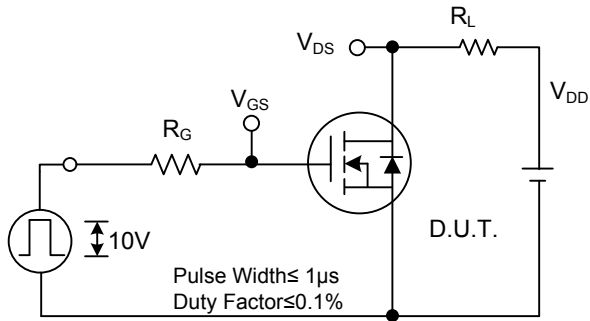


Peak Diode Recovery dv/dt Test Circuit

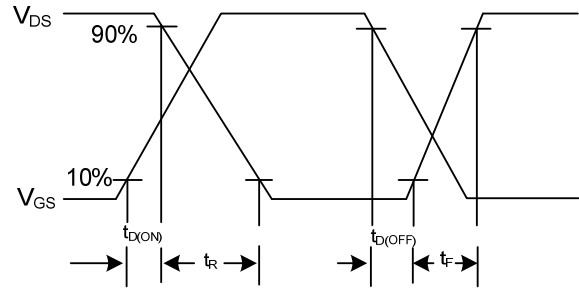


Peak Diode Recovery dv/dt Waveforms

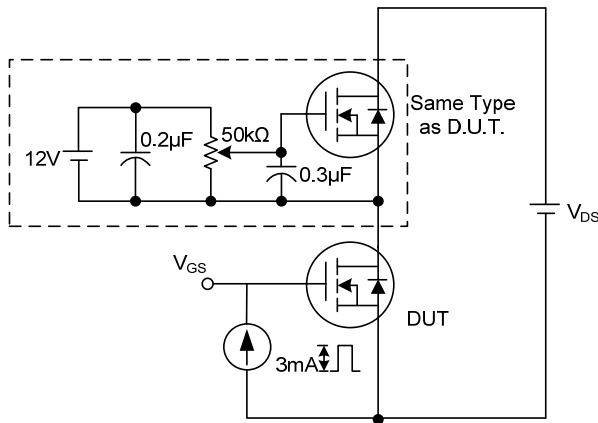
TEST CIRCUITS AND WAVEFORMS (Cont.)



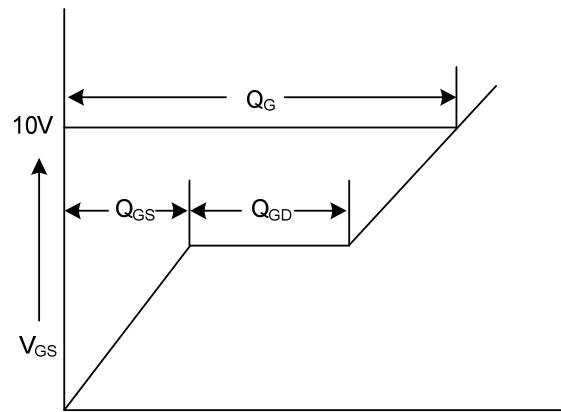
Switching Test Circuit



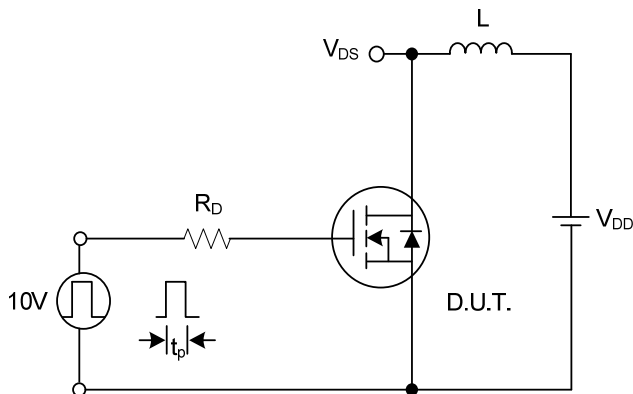
Switching Waveforms



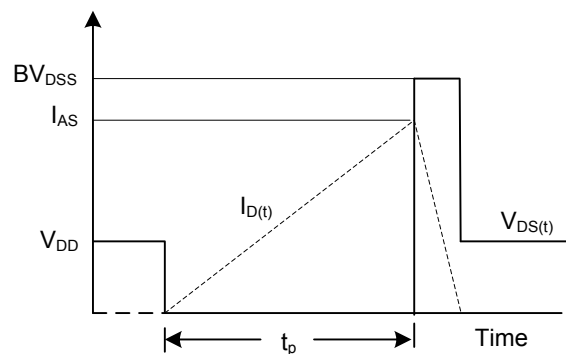
Gate Charge Test Circuit



Gate Charge Waveform

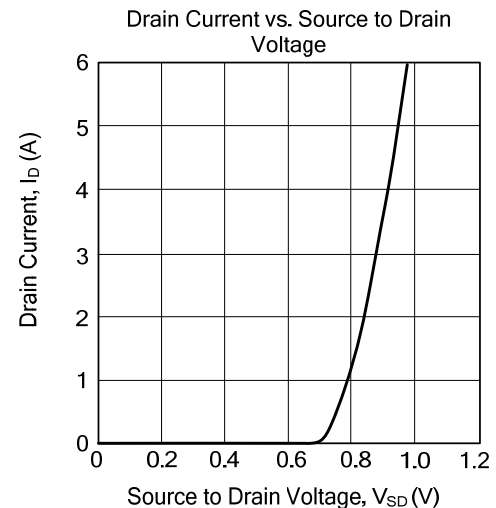
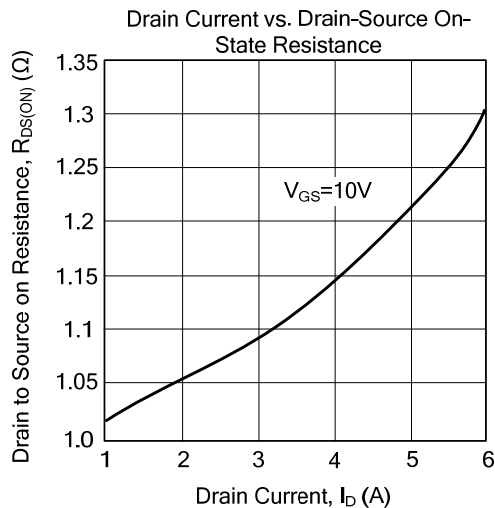
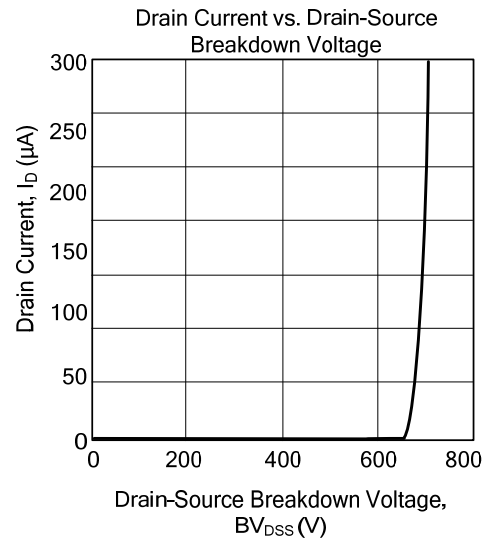
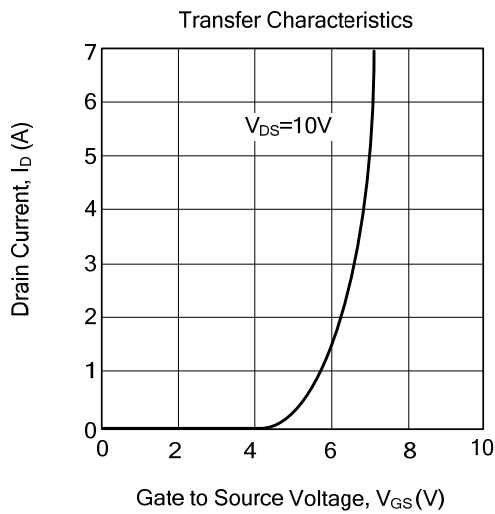


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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